

600V/600A HALF BRIDGE PEM

4801

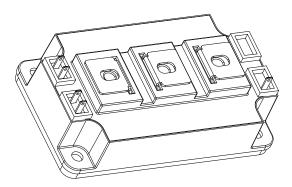
MIL-PRF-38534 CERTIFIED

4707 Dey Road Liverpool, N.Y. 13088

(315) 701-6751

FEATURES:

- · Half Bridge Configuration
- · 600V Rated Voltage
- 600A Continuous Output Current
- Internal Zener Clamps on Gates
- Proprietary Encapsulation Provides Near Hermetic Performance
- MIL-PRF-38534 Screening Available (Modified)
- · Light Weight Ultra-Flat AISiC Baseplate
- · Robust Mechanical Design for Hi-Rel Applications
- · Ultra-Low Inductance Internal Layout
- Withstands HAST and Thermal Cycling (-55°C to +125°C)
- · High Side Collector Sense Pin for De-Sat Detection



DESCRIPTION:

The MSK 4801 is one of a family of Plastic Encapsulated Modules (PEM) developed specifically for use in military, aerospace and other severe environment applications. The half bridge configuration and 600 volt/600 amp rating make it ideal for use in high current motor drive and inverter applications. The Aluminum Silicon Carbide (AlSiC) baseplate offers superior flatness and light weight; far better than the copper or copper alloys found in most high power plastic modules. The high thermal conductivity materials used to construct the MSK 4801 allow high power outputs at elevated baseplate temperatures. Our proprietary coating, SEES™ - Severe Environment Encapsulation System - protects the internal circuitry of MSK PEM's from moisture and contamination, allowing them to pass the rugged environmental screening requirements of military and aerospace applications. MSK PEM's are also available with industry standard silicone gel coatings for a lower cost option.

EQUIVALENT SCHEMATIC (+)C1C10-**R**1 Q1 D1 **G1**0 R2 1 VR2 ○ (AC)C2E1 187 E10 R3 Q2 **本** D2 G2 O R4 VR3 18V ->(−)E2 1 VR4 187 E20

TYPICAL APPLICATIONS

- · Motor Drives
- Inverters

ABSOLUTE MAXIMUM RATING

Vce	Collector to Emitter Voltage	. 600V	Tst	Storage Temperature Range55°C to +125°C
Vge	Gate to Emitter Voltage	. ±20V	TJ	Junction Temperature
Iout	Current (Continuous)	. 600A	Tc	Case Operating Temperature Range
IOUTP	Current Pulsed (1mS)	. 1200A		MSK 4801H/E55°C to +125°C
	Case Isolation Voltage			MSK 480140°C to +85°C

ELECTRICAL SPECIFICATIONS

Parameter (6)	Test Conditions	Group A	MSK 4801 H/E			MSK 4801			Units
Tarameter &	103t Conditions	Subgroup	Min.	Тур.	Max.	Min.	Тур.	Max.	Onits
	e IC=600A, VGE=15V	1	-	1.9	2.5	-	1.9	2.7	V
Collector-Emitter Saturation Voltage		2	-	1.9	2.5	-	1.9	2.7	V
		3	-	1.9	2.6	-	1.9	3.0	V
	VCE=600V, VGE=0V	1	-	0.15	2.5	-	0.15	3.0	mΑ
Collector-Emitter Leakage Current		2	-	6.0	15	-	6.0	15	mΑ
		3 (1)	-	-	2.5	1	-	3.0	mΑ
		1	4.0	5.4	7.5	4.0	5.4	7.5	٧
Gate Threshold Voltage	IC = 30mA, $VCE = VGE$	2	3.0	4.2	7.5	3.0	4.2	7.5	٧
		3	4.0	6.0	7.5	4.0	6.0	7.5	V
	VCE=0V, VGE= ±15V	1	-0.5	<1nA	0.5	-0.7	<1nA	0.7	ųΑ
Gate Leakage Current		2	-0.5	<1nA	0.5	-0.7	<1nA	0.7	uA
		3	-0.5	<1nA	0.5	-0.7	<1nA	0.7	uA
	IC = 600A	1	-	1.9	2.6	-	1.9	2.8	V
Diode Forward Voltage		2	-	1.5	2.0	-	1.5	2.2	٧
		3	-	2.2	2.9	-	2.2	3.1	V
Total Gate Charge ①	V = 300V, $IC = 600A$	4	-	4500	5380	-	4500	5380	nC
Turn-On Delay ①	$V = 300V$, IC = 600A, RG = 20 Ω	4	-	820	950	-	820	970	n\$
Rise Time ①	$V = 300V$, $IC = 600A$, $RG = 20\Omega$	4	-	400	700	-	400	700	nS
Turn-Off Delay ①	$V = 300V$, IC = 600A, RG = 10Ω	4	-	2.0	2.1	-	2.0	2.1	uS
Fall Time ①	$V = 300V$, $IC = 600A$, $RG = 10\Omega$	4	-	140	300	-	140	300	nS
Diode Reverse Recovery Time 1	IE = 450A, di/dt = 900A/uS	4	-	80	110	-	80	170	nS
Diode Reverse Recovery Charge ①	IE = 450A, di/dt = 900A/uS	4	-	3.3	3.48	-	3.3	3.48	uC
Thermal Resistance (1)	IGBT @ TJ=125°C	4	-	0.05	0.06	-	0.05	0.07	°C/W
mermal nesistance ()	DIODE @ TJ = 125°C	4	-	0.09	0.12	-	0.09	0.13	°C/W

NOTES:

- ① Guaranteed by design but not tested. Typical parameters are representative of actual device performance but are for reference only.
 ② Industrial grade and "E" suffix devices shall be tested to subgroup 1 unless otherwise specified.
 ③ Military grade devices ("H" suffix) shall be 100% tested to subgroups 1, 2 and 3.
 ④ Subgroups 4, 5 and 6 testing available upon request.
 ⑤ Subgroup 1, 4 TA = +25°C

- - $2, 5 \text{ TA} = +125^{\circ}\text{C}$
 - 3, 6 TA = -55 °C
- 6 All specifications apply to both the upper and lower sections of the half bridge. 7 VGE = 15V unless otherwise specified.

APPLICATION NOTES

TBD

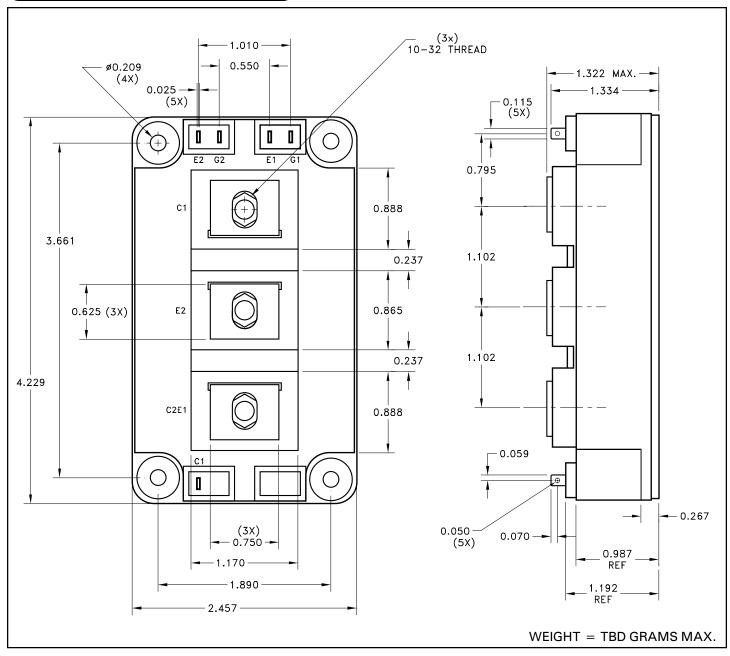
TYPICAL PERFORMANCE CURVES

TBD

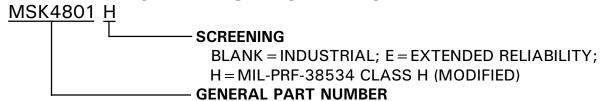
SCREENING CHART

OPERATION IN ACCORDANCE WITH MIL-PRF-38534	INDUSTRIAL	CLASS E	CLASS H	
QUALIFICATION (MODIFIED)	NO	NO	YES	
ELEMENT EVALUATION	NO	YES	YES	
CLEAN ROOM PROCESSING	YES	YES	YES	
NON DESTRUCT BOND PULL SAMPLE	YES	YES	YES	
CERTIFIED OPERATORS	NO	YES	YES	
MIL LINE PROCESSING	YES	YES	YES	
MAX REWORK SPECIFIED	NO	YES	YES	
ENCAPSULANT	GEL COAT	SEES TM	SEES TM	
PRE-CAP VISUAL	YES - INDUSTRIAL	YES - CLASS H	YES - CLASS H	
TEMP CYCLE (-55°C TO +125°C)	NO	YES	YES	
BURN-IN	NO	YES - 96 HOURS	YES - 160 HOURS	
ELECTRICAL TESTING	YES - 25°C	YES - 25°C	YES - FULL TEMP	
EXTERNAL VISUAL	YES - SAMPLE	YES - SAMPLE	YES	
XRAY	NO	NO	NO	
PIN FINISH	NI	NI	NI	

NOTE: ADDITIONAL SCREENING IS AVAILABLE SUCH AS XRAY, CSAM, MECHANICAL SHOCK, ETC. CONTACT FACTORY FOR QUAL STATUS.



ORDERING INFORMATION



THE ABOVE EXAMPLE IS A MILITARY SCREENED MODULE.

M.S. Kennedy Corp.

4707 Dey Road Liverpool, New York 13088 Phone (315) 701-6751 FAX (315) 701-6752 www.mskennedy.com

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